NSN 5961-01-452-8757

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-452-8757 **Inclosure Material:** Glass **Overall Length:** Between 0.120 inches and 0.300 inches **Terminal Length:** 1.000 inches **Overall Diameter:** Between 0.060 inches and 0.107 inches **End Application:** Joint stars e/i fscm 81349 **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 6.4 regulator voltage **Voltage Tolerance In Percent:** -5.0/+5.0 **Current Rating Per Characteristic:** 0.50 milliamperes all primaries horsepower metric and 70.00 milliamperes repetitive peak forward current **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

Fiig: A110a0 Mil-std (military Standard):

Mil-prf-19500 spec.